



2SC4467

NPN EPITAXIAL SILICON TRANSISTOR

SILICON NPN TRIPLE DIFFUSED PLANAR TRANSISTOR

DESCRIPTION

The UTC **2SC4467** is a silicon NPN triple diffused planar transistor, it uses UTC's advanced technology to provide the customers with high DC current gain and high collector-base breakdown voltage, etc.

The UTC **2SC4467** is suitable for audio and general purpose, etc.

FEATURES

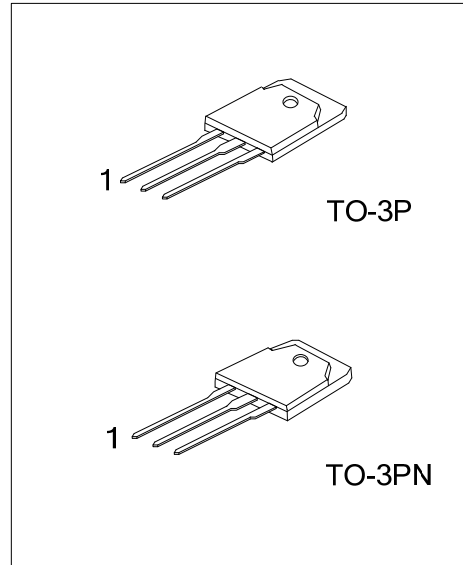
- * High DC current gain
- * High collector-base breakdown voltage

ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
2SC4467L-x-T3P-T	2SC4467G-x-T3P-T	TO-3P	B	C	E	Tube
2SC4467L-x-T3N-T	2SC4467G-x-T3N-T	TO-3PN	B	C	E	Tube

Note: Pin Assignment: B: Base C: Collector E: Emitter

<p>2SC4467L-x-T3P-T</p>	<p>(1) T: Tube</p> <p>(2) T3P: TO-3P, T3N: TO-3PN</p> <p>(3) x: reference to Classification of h_{FE}</p> <p>(4) L: Lead Free, G: Halogen Free</p>
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■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V _{CBO}	160	V
Collector-Emitter Voltage	V _{CEO}	120	V
Emitter-Base Voltage	V _{EBO}	6	V
Collector Current	I _C	8	A
Base Current	I _B	3	A
Collector Power Dissipation (T _C =25°C)	P _C	80	W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55 ~150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

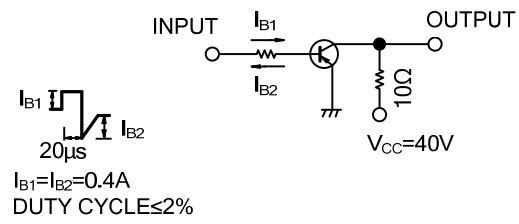
■ ELECTRICAL CHARACTERISTICS (T_A=25°C)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Cut-Off Current	I _{CBO}	V _{CB} =160V			10	μA
Emitter Cut-Off Current	I _{EBO}	V _{EB} =6V			10	μA
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C =50mA	120			V
DC Current Gain	h _{FE}	V _{CE} =4V, I _C =3A	50			
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =3A, I _B =0.3A			1.5	V
Current Gain Bandwidth Product	f _T	V _{CE} =12V, I _E =-0.5A		20		MHz
Output Capacitance	C _{ob}	V _{CB} =10V, f=1MHz		200		pF
Switching time	Turn-on time	V _{CC} =40V, R _L =10Ω, I _C =4A, I _{B1} =0.4A I _{B2} =0.4A		0.13		μS
	Storage time			3.50		μS
	Fall time			0.32		μS

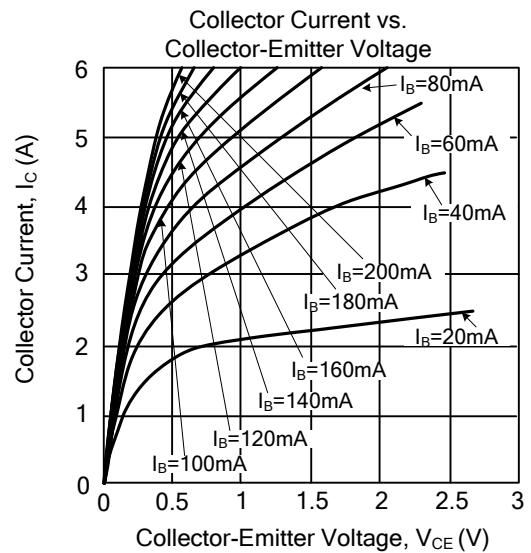
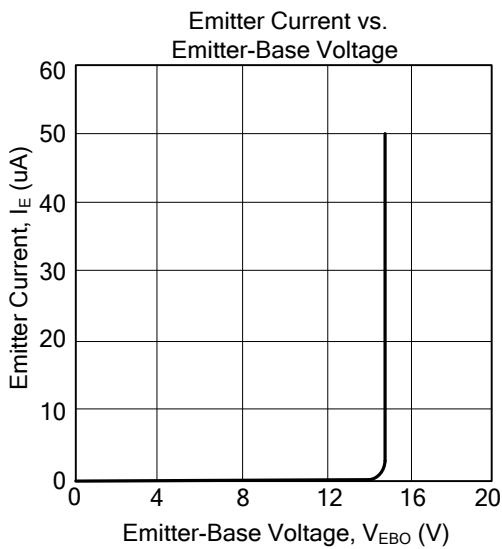
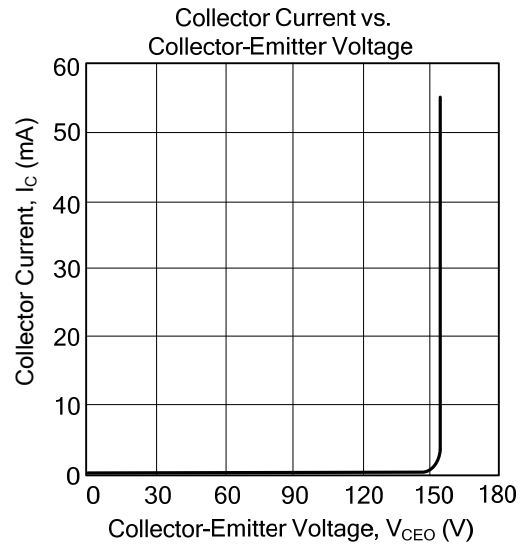
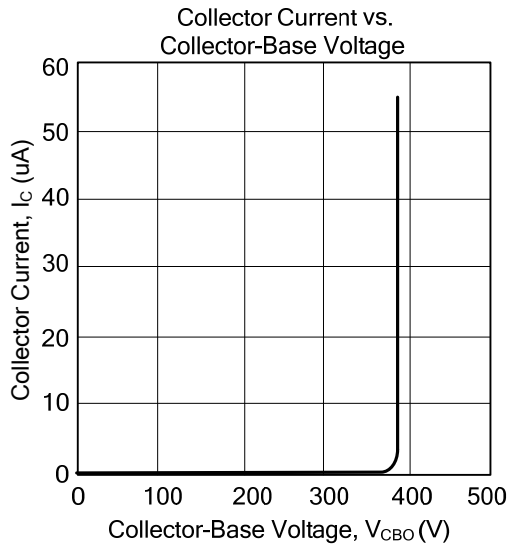
■ CLASSIFICATION OF h_{FE}

RANK	O	P	Y
RANGE	50~100	70~140	90~180

■ TEST CIRCUIT



TYPICAL CHARACTERISTICS



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